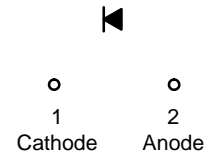


S **Ca b de (S C)**
Sc **D de E eS C,**
10 A, 650 V, D2, TO-247-2L

FFSH1065B-F085



Schottky Diode

Description

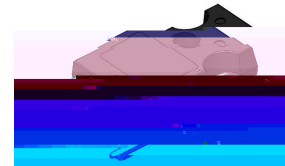
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 51 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

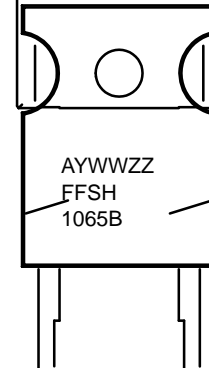
Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



TO-247-2LD
CASE 340DA

MARKING DIAGRAM



- | | |
|-----------|---------------------------|
| A | = Assembly Plant Code |
| YWW | = Date Code (Year & Week) |
| ZZ | = Lot Code |
| FFSH1065B | = Specific Device Code |

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSH1065B-F085

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	51	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 142°C	10	A	
	Continuous Rectified Forward Current @ T _C < 135°C	11.5		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	600	A
		T _C = 150°C, 10 μs	535	A
I _{F, SM}	Non-Repetitive Forward Surge Current T _C = 25°C	Half-Sine Pulse, t _p = 8.3 ms	42	A
P _{tot}	Power Dissipation	T _C = 25°C	83	W
		T _C = 150°C	14	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	
	TO247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 51 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 14.5 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max	1.81	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.5	1.7	V
		I _F = 10 A, T _C = 125°C	-	1.7	2.0	
		I _F = 10 A, T _C = 175°C	-	2	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	0.5	40	μA
		V _R = 650 V, T _C = 125°C	-	1	80	
		V _R = 650 V, T _C = 175°C	-	2	160	
Q _C	Total Capacitive Charge	V = 400 V	-	25	-	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	-	421	-	pF
		V _R = 200 V, f = 100 kHz	-	40	-	
		V _R = 400 V, f = 100 kHz	-	34	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH1065B-F085	59.754 1ma0097167B 0 01 9a4637 0 TD0 Tc<009Tcw[85		

FFSH1065B-F085

TYPICAL CHARACTERISTICS
($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Figure 7. Capacitance Stored Energy

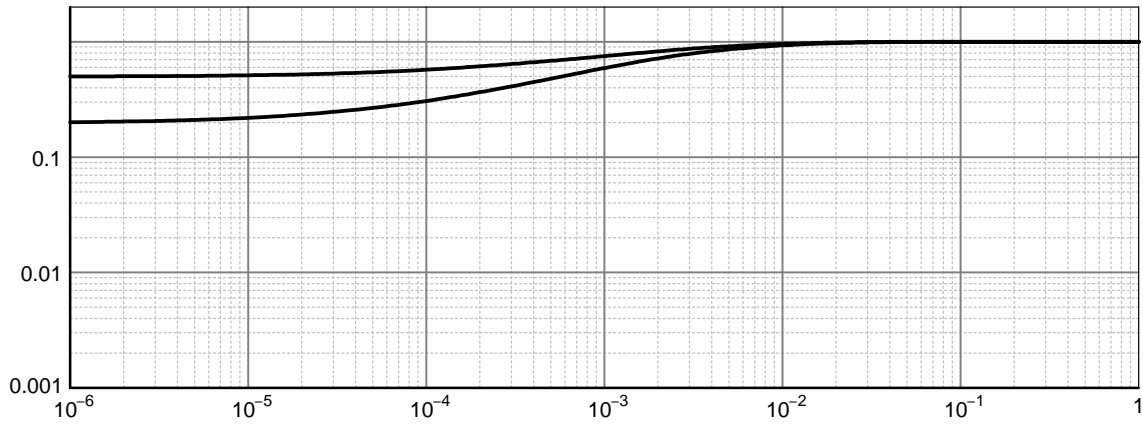


Figure 8. Junction-to-Case Transient Thermal Response Curve

**TO-247-2LD
CASE 340DA
ISSUE A**

DATE 27 FEB 2019

**GENERIC
MARKING DIAGRAM***

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